

2SB1189 / Descriptions

SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

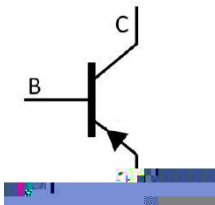
2SB1189 / Features

Complements the 2SD1767,
Low $V_{CE(sat)}$, complements the 2SD1767.

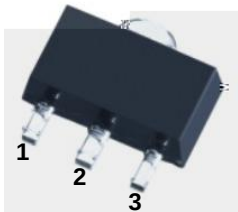
2SB1189 / Applications

Medium power amplifier applications.

2SB1189 / Equivalent Circuit



2SB1189 / Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

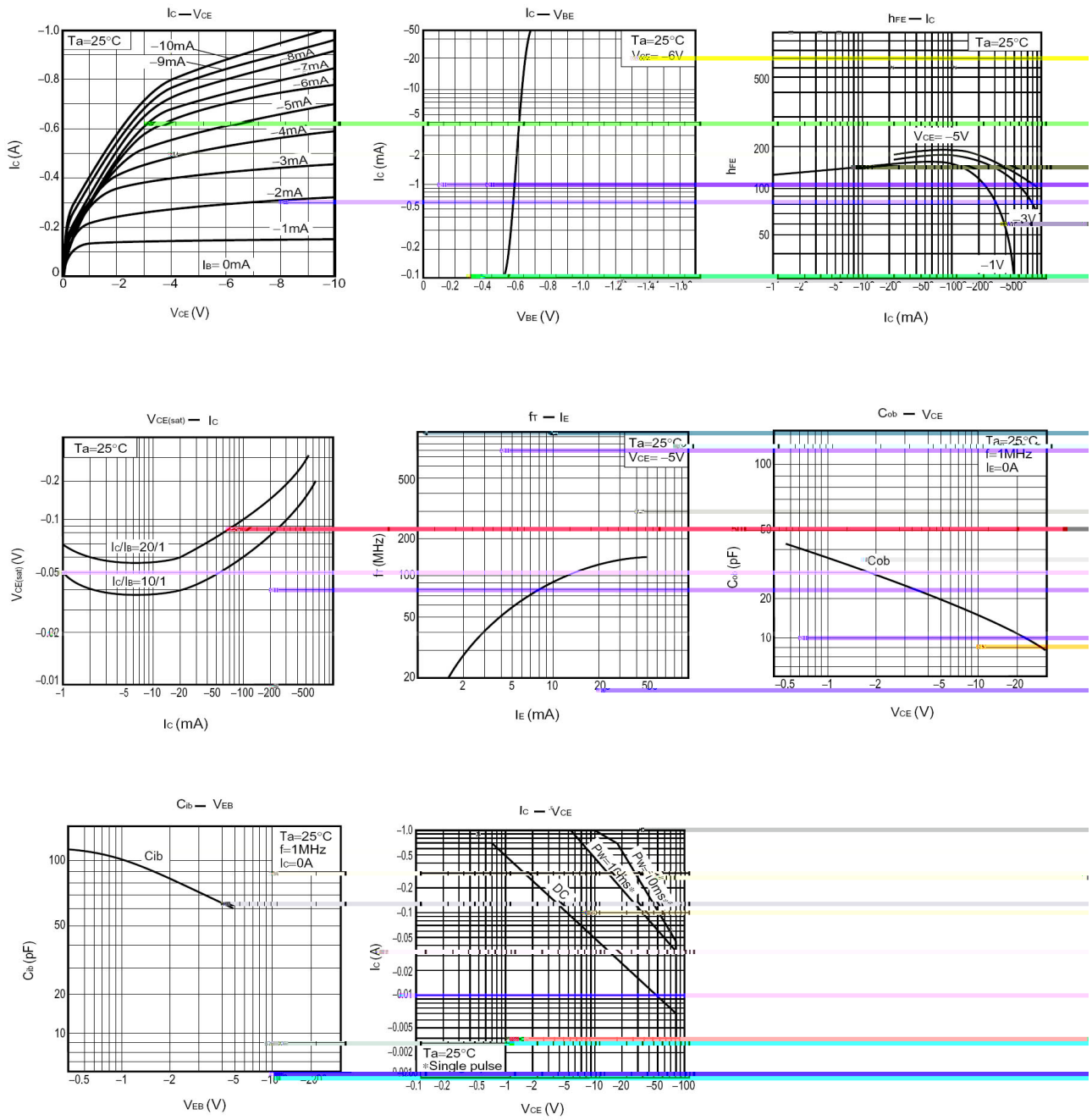
2SB1189 / Marking

h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390
Marking	HBDP*	HBDQ*	HBDR*

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V

Colle

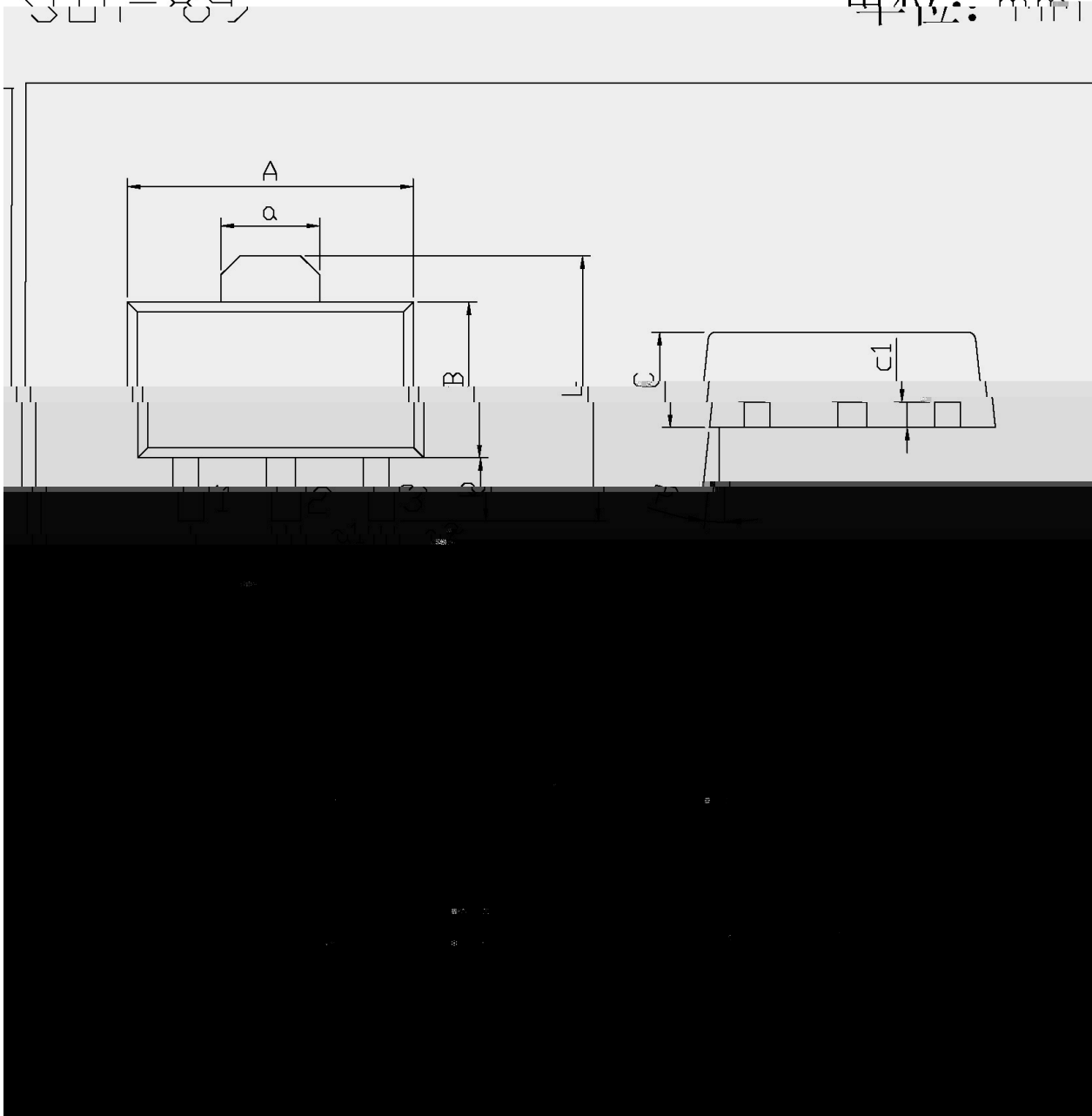
Electrical Characteristic Curve



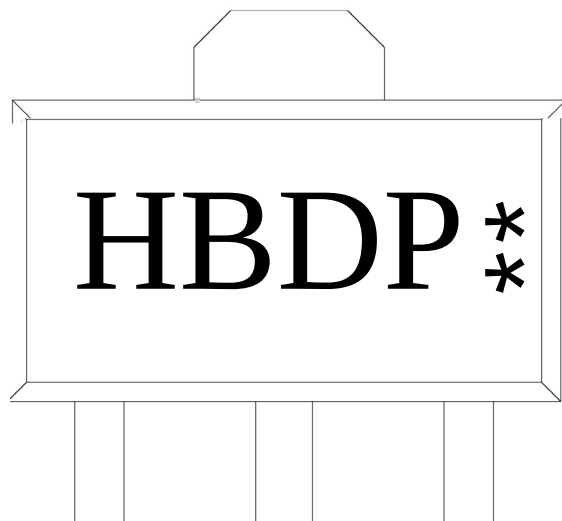
⊂ É Ò Ì ¢ / Package Dimensions

⊂ É Ò Ì ¢

单位: mm



1. 1.1 / Marking Instructions



H

BD

P h_{FE}

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Note:

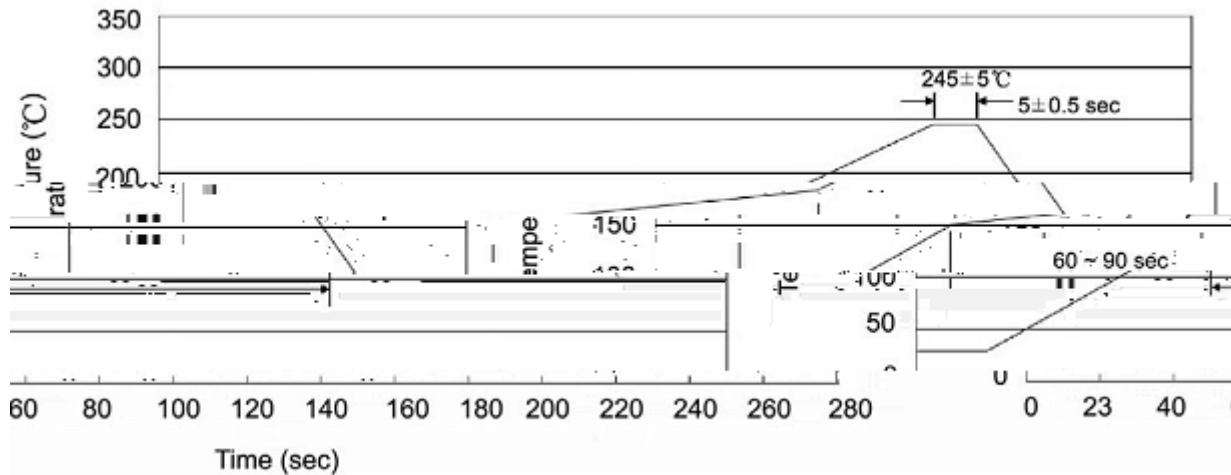
H: Company Code.

BD: Product Type.

P h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No.

Whp shudwxuh Suriloh i ru LU Uhior z Vroghulq j+Se0l uhh,



Note:

1. Preheating: 25~150 , Time: 60~90sec.
2. Peak Temp.: 245±5 , Duration: 5±0.5sec.
3. Cooling Speed: 2~10 /sec.

Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.: 260±5 Time: 10±1 sec

Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-89	1,000	7	7,000	8	56,000	7 ×12	180×120×180	385×257×392

Notices